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**Superprevodnost - 15. del: Meritve elektronskih karakteristik - Lastna površinska impedanca superprevodnih plasti pri mikrovalovnih frekvencah**

Superconductivity - Part 15: Electronic characteristic measurements - Intrinsic surface impedance of superconductor films at microwave frequencies

Supraleitfähigkeit - Teil 15: Messungen der elektronischen Charakteristik - Oberflächenimpedanz von Supraleiterschichten bei Mikrowellenfrequenzen

Supraconductivité - Partie 15: Mesures de caractéristiques électroniques - Impédance de surface intrinsèque de films supraconducteurs aux fréquences micro-ondes

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**Ta slovenski standard je istoveten z: EN 61788-15:2011**

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**ICS:**

17.220.20	Merjenje električnih in magnetnih veličin	Measurement of electrical and magnetic quantities
29.050	Superprevodnost in prevodni materiali	Superconductivity and conducting materials

**SIST EN 61788-15:2012****en**

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EUROPEAN STANDARD  
NORME EUROPÉENNE  
EUROPÄISCHE NORM

**EN 61788-15**

December 2011

ICS 29.050

English version

**Superconductivity -  
Part 15: Electronic characteristic measurements -  
Intrinsic surface impedance of superconductor films at microwave  
frequencies  
(IEC 61788-15:2011)**

Supraconductivité -  
Partie 15: Mesures de caractéristiques  
électroniques -  
Impédance de surface intrinsèque de films  
supraconducteurs aux fréquences micro-  
ondes  
(CEI 61788-15:2011)

Supraleitfähigkeit -  
Teil 15: Messungen der elektronischen  
Charakteristik -  
Oberflächenimpedanz von  
Supraleiterschichten bei  
Mikrowellenfrequenzen  
(IEC 61788-15:2011)

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Comité Européen de Normalisation Electrotechnique  
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**Management Centre: Avenue Marnix 17, B - 1000 Brussels**

## Foreword

The text of document 90/280/FDIS, future edition 1 of IEC 61788-15, prepared by IEC/TC 90 "Superconductivity" was submitted to the IEC-CENELEC parallel vote and approved by CENELEC as EN 61788-15:2011.

The following dates are fixed:

- latest date by which the document has to be implemented at national level by publication of an identical national standard or by endorsement (dop) 2012-08-28
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## Annex ZA (normative)

### Normative references to international publications with their corresponding European publications

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NOTE When an international publication has been modified by common modifications, indicated by (mod), the relevant EN/HD applies.

<u>Publication</u>	<u>Year</u>	<u>Title</u>	<u>EN/HD</u>	<u>Year</u>
IEC 60050-815	2000	International Electrotechnical Vocabulary (IEV) - Part 815: Superconductivity	-	-
IEC 61788-7	2006	Superconductivity - Part 7: Electronic characteristic measurements - Surface resistance of superconductors at microwave frequencies	EN 61788-7	2006

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IEC 61788-15

Edition 1.0 2011-10

# INTERNATIONAL STANDARD

## NORME INTERNATIONALE



**Superconductivity –** **STANDARD PREVIEW**  
**Part 15: Electronic characteristic measurements – Intrinsic surface impedance**  
**of superconductor films at microwave frequencies**

[SIST EN 61788-15:2012](https://standards.iteh.ai/catalog/standards/sist/8ac6534a-8e1a-402f-8297-)

**Supraconductivité –**  
**Partie 15: Mesures de caractéristiques électroniques – Impédance de surface**  
**intrinsèque de films supraconducteurs aux fréquences micro-ondes**

INTERNATIONAL  
ELECTROTECHNICAL  
COMMISSION

COMMISSION  
ELECTROTECHNIQUE  
INTERNATIONALE

PRICE CODE  
CODE PRIX



ICS 29.050

ISBN 978-2-88912-710-8

## CONTENTS

FOREWORD.....	4
INTRODUCTION.....	6
1 Scope.....	7
2 Normative references.....	7
3 Terms and definitions.....	7
4 Requirements.....	8
5 Apparatus.....	9
5.1 Measurement equipment.....	9
5.2 Measurement apparatus.....	9
5.3 Dielectric rods.....	13
5.4 Superconductor films and copper cavity.....	14
6 Measurement procedure.....	14
6.1 Set-up.....	14
6.2 Measurement of the reference level.....	14
6.3 Measurement of the $R_S$ of oxygen-free high purity copper.....	14
6.4 Determination of the effective $R_S$ of superconductor films and $\tan\delta$ of standard dielectric rods.....	17
6.5 Determination of the penetration depth.....	18
6.6 Determination of the intrinsic surface impedance.....	20
7 Uncertainty of the test method.....	21
7.1 Measurement of unloaded quality factor.....	21
7.2 Measurement of loss tangent.....	21
7.3 Temperature.....	22
7.4 Specimen and holder support structure.....	22
8 Test Report.....	22
8.1 Identification of test specimen.....	22
8.2 Report of the intrinsic $Z_S$ values.....	22
8.3 Report of the test conditions.....	22
Annex A (informative) Additional information relating to clauses 1 to 8.....	24
Annex B (informative) Uncertainty considerations.....	41
Bibliography.....	45
Figure 1 – Schematic diagram for the measurement equipment for the intrinsic $Z_S$ of HTS films at cryogenic temperatures.....	10
Figure 2 – Schematic diagram of a dielectric resonator with a switch for thermal connection.....	10
Figure 3 – Typical dielectric resonator with a movable top plate.....	11
Figure 4 – Switch block for thermal connection.....	12
Figure 5 – Dielectric resonator assembled with a switch block for thermal connection.....	13
Figure 6 – A typical resonance peak. Insertion attenuation $IA$ , resonant frequency $f_0$ and half power bandwidth $\Delta f_{3dB}$ are defined.....	16
Figure 7 – Reflection scattering parameters $S_{11}$ and $S_{22}$ .....	18
Figure 8 – Definitions for terms in Table 5.....	22
Figure A.1 – Schematic diagram for the measurement system.....	24
Figure A.2 – A motion stage using step motors.....	25



Figure A.3 – Cross-sectional view of a dielectric resonator .....	26
Figure A.4 – A diagram for simplified cross-sectional view of a dielectric resonator .....	30
Figure A.5 – Mode chart for a sapphire resonator .....	33
Figure A.6 – Frequency response of the sapphire resonator.....	34
Figure A.7 – $Q_U$ versus temperature for the $TE_{021}$ and the $TE_{012}$ modes of the sapphire resonator with 360 nm-thick YBCO films .....	35
Figure A.8 – The resonant frequency $f_0$ versus temperature for the $TE_{021}$ and $TE_{012}$ modes of the sapphire resonator with 360 nm-thick YBCO films.....	35
Figure A.9 – The temperature dependence of the $R_{Se}$ of YBCO films with the thicknesses of 70 nm to 360 nm measured at ~40 GHz.....	36
Figure A.10 – The temperature dependence of $\Delta\lambda_e$ for the YBCO films with the thicknesses of 70 nm and 360 nm measured at ~40 GHz.....	36
Figure A.11 – The penetration depths $\lambda$ of the 360 nm-thick YBCO film measured at 10 kHz by using the mutual inductance method and at ~40 GHz by using sapphire resonator .....	37
Figure A.12 – The temperature dependence of the intrinsic surface resistance $R_S$ of YBCO films with the thicknesses of 70 nm to 360 nm measured at ~40 GHz.....	37
Figure A.13 – Comparison of the temperature-dependent value of each term in Equation (A.35) for the $TE_{021}$ mode of the standard sapphire resonator.....	38
Figure A.14 – Comparison of the temperature-dependent value of each term in Equation (A.35) for the $TE_{012}$ mode of the standard sapphire resonator.....	38
Figure A.15 – Temperature dependence of uncertainty in the measured intrinsic $R_S$ of YBCO films.....	39
SIST EN 61788-15:2012 <a href="https://standards.iteh.ai/catalog/standards/sist/8ac6534a-8e1a-402f-8297-0f1ca4c1e307/en-61788-15-2012">https://standards.iteh.ai/catalog/standards/sist/8ac6534a-8e1a-402f-8297-0f1ca4c1e307/en-61788-15-2012</a>	
Table 1 – Typical dimensions of a sapphire rod .....	14
Table 2 – Typical dimensions of OFHC cavities and HTS films.....	14
Table 3 – Geometrical factors and filling factors calculated for the standard sapphire resonator .....	17
Table 4 – Specifications of vector network analyzer.....	21
Table 5 – Type B uncertainty for the specifications on the sapphire rod .....	21
Table A.1 – Geometrical factors and filling factors calculated for the standard sapphire resonator .....	31
Table B.1 – Output signals from two nominally identical extensometers .....	42
Table B.2 – Mean values of two output signals .....	42
Table B.3 – Experimental standard deviations of two output signals.....	42
Table B.4 – Standard uncertainties of two output signals .....	42
Table B.5 – Coefficient of variations of two output signals.....	43

## INTERNATIONAL ELECTROTECHNICAL COMMISSION

## SUPERCONDUCTIVITY –

**Part 15: Electronic characteristic measurements –  
Intrinsic surface impedance of superconductor  
films at microwave frequencies**

## FOREWORD

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International Standard IEC 61788-15 has been prepared by IEC technical committee 90: Superconductivity.

The text of this standard is based on the following documents:

FDIS	Report on voting
90/280/FDIS	90/283/RVD

Full information on the voting for the approval of this standard can be found in the report on voting indicated in the above table.

This publication has been drafted in accordance with the ISO/IEC Directives, Part 2.

A list of all parts of the IEC 61788 series, published under the general title *Superconductivity*, can be found on the IEC website.

The committee has decided that the contents of this publication will remain unchanged until the stability date indicated on the IEC web site under "<http://webstore.iec.ch>" in the data related to the specific publication. At this date, the publication will be

- reconfirmed,
- withdrawn,
- replaced by a revised edition, or
- amended.

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## INTRODUCTION

Since the discovery of high  $T_C$  superconductors (HTS), extensive research has been performed worldwide on electronic applications and large-scale applications with HTS filter subsystems based on  $\text{YBa}_2\text{Cu}_3\text{O}_{7-\delta}$  (YBCO) having already been commercialized [1]<sup>1</sup>.

The merits of using HTS films for microwave devices such as resonators, filters, antennas, delay lines, etc., include i) possibility of microwave losses from HTS films being extremely low and ii) no signal dispersion on transmission lines made of HTS films due to extremely low microwave surface resistance ( $R_S$ ) [2] and frequency-independent penetration depth ( $\lambda$ ) of HTS films, respectively.

In this regard, when it comes to designing HTS-based microwave devices, it is important to measure the surface impedance ( $Z_S$ ) of HTS films with  $Z_S = R_S + jX_S$  and  $X_S = \omega\mu_0\lambda$  (here  $\omega$  and  $\mu_0$  denote the angular frequency and the permeability of vacuum, respectively,  $X_S$ , the surface reactance, and  $X_S = \omega\mu_0\lambda$  is valid at temperatures not too close to the critical temperature  $T_C$  of HTS films).

Various reports have been made on measuring the  $R_S$  of HTS films at microwave frequencies with the typical  $R_S$  of HTS films as low as 1/100 - 1/50 of that of oxygen-free high-purity copper (OFHC) at 77 K and 10 GHz. The  $R_S$  of conventional superconductors such as niobium (Nb) could be easily measured by using Nb cavities by converting the resonator quality factor ( $Q$ ) to the  $R_S$  of Nb. However, such conventional measurement method could no longer be applied to HTS films grown on dielectric substrates with which it is basically impossible to make all-HTS cavities. Instead, for measuring the  $R_S$  of HTS films, several other methods have been useful, which include the microstrip resonator method [3], the coplanar microstrip resonator method [4], the parallel plate resonator method [5] and the dielectric resonator method [7-10]. Among the stated methods, the dielectric resonator method has been very useful due to that the method enables to measure the  $R_S$  in a non-invasive way and with accuracy. In 2002, the International Electrotechnical Commission (IEC) published the dielectric resonator method as a measurement standard [11].

The test method given in this standard enables measurement not only of the intrinsic surface resistance but also the intrinsic surface reactance of HTS films, regardless of the film's thickness, by using a single sapphire resonator that differs from the existing IEC standard (IEC 61788-7:2006), which is limited to measuring the surface resistance of superconductor films having a thicknesses of more than  $3\lambda$  at the measured temperature by using two sapphire resonators. In fact, the measured surface resistances of HTS films with different thicknesses of less than  $3\lambda$  mean effective values instead of intrinsic values, which cannot be used for directly comparing the microwave properties of HTS films among one another [12, 13]. Use of a single sapphire resonator as suggested in this standard also makes it possible to reduce uncertainty in the measured surface resistance that might result from using two sapphire resonators with sapphire rods of even slightly different quality.

The test method given in this standard can also be applied to HTS coated conductors, HTS bulks and other superconductors having established models for the penetration depth.

This standard is intended to provide an appropriate and agreeable technical base for the time being to engineers working in the fields of electronics and superconductivity technology.

The test method covered in this standard has been discussed at the VAMAS (Versailles Project on Advanced Materials and Standards) TWA-16 meeting.

<sup>1</sup> Numerals in square brackets refer to the Bibliography.

## SUPERCONDUCTIVITY –

### Part 15: Electronic characteristic measurements – Intrinsic surface impedance of superconductor films at microwave frequencies

#### 1 Scope

This part of IEC 61788 describes measurements of the intrinsic surface impedance ( $Z_S$ ) of HTS films at microwave frequencies by a modified two-resonance mode dielectric resonator method [13, 14]<sup>2</sup>. The object of measurement is to obtain the temperature dependence of the intrinsic  $Z_S$  at the resonant frequency  $f_0$ .

The frequency and thickness range and the measurement resolution for the intrinsic  $Z_S$  of HTS films are as follows:

- frequency: up to 40 GHz;
- film thickness: greater than 50 nm;
- measurement resolution: 0,01 m $\Omega$  at 10 GHz.

The intrinsic  $Z_S$  data at the measured frequency, and that scaled to 10 GHz, assuming the  $f^2$  rule for the intrinsic surface resistance  $R_S$  ( $f < 40$  GHz) and the  $f$  rule for the intrinsic surface reactance  $X_S$  for comparison, shall be reported.

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#### 2 Normative references

The following referenced documents are indispensable for the application of this document. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

IEC 60050-815:2000, *International Electrotechnical Vocabulary – Part 815: Superconductivity*

IEC 61788-7:2006, *Superconductivity – Part 7: Electronic characteristic measurements – Surface resistance of superconductors at microwave frequencies*

#### 3 Terms, definitions and general concepts

##### 3.1 Terms and definitions

For the purposes of this document, the definitions given in IEC 60050-815, one of which is repeated here for convenience, apply.

##### 3.1.1

##### surface impedance

impedance of a material for high frequency electromagnetic wave which is constrained to the surface of the material in case of metals and superconductors

NOTE The surface impedance governs the thermal losses of superconducting RF cavities.

<sup>2</sup> Numerals in square brackets refer to the Bibliography.

(IEC 60050-815:2000, 815-04-62)

### 3.2 General concepts

#### 3.2.1 Intrinsic surface impedance

In general, the surface impedance  $Z_S$  of conductors, including superconductors, is defined as the ratio of the tangential component of the electric field ( $E_t$ ) and that of the magnetic field ( $H_t$ ) at a conductor surface:

$$Z_S = \frac{E_t}{H_t} = R_S + jX_S. \quad (1)$$

Here  $R_S$  denotes the surface resistance and  $X_S$ , the surface reactance. If the thickness of the conductor (or the superconductor) under test is sufficiently greater than the penetration depth of electromagnetic fields,  $Z_S$  is expressed by

$$Z_S = \left( \frac{\mu}{\varepsilon} \right)^{\frac{1}{2}} = \left( \frac{j\mu_0\omega}{\sigma} \right)^{\frac{1}{2}} \quad (2)$$

with  $\varepsilon$  and  $\mu$  denoting the permittivity and the permeability of the conductor (or the superconductor) under test, respectively,  $\mu_0$ , the permeability of vacuum,  $\sigma$ , the conductivity of the conductor (or the superconductor), and  $\omega$ , the measured angular frequency, and is called the intrinsic surface impedance.  $\sigma$  is real for the conductor and complex for the superconductor.

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#### 3.2.2 Effective surface impedance

If the thickness of the conductor (or the superconductor) under test is not sufficiently greater than the penetration depth of electromagnetic fields,  $Z_S$  as defined by Equation (1) in 3.2.1 becomes significantly different from that defined by Equation (2) in 3.2.1. In this case,  $Z_S$  as defined by Equation (1) is called the effective surface impedance  $Z_{Se}$  with

$$Z_{Se} = \frac{E_t}{H_t} = R_{Se} + jX_{Se} \quad (3)$$

Here  $R_{Se}$  denotes the effective surface resistance and  $X_{Se}$ , the effective surface reactance.

## 4 Requirements

The  $Z_S$  of HTS films shall be measured by applying a microwave signal to a dielectric resonator with the superconductor specimen and then measuring the attenuation of the resonator at each frequency. The frequency shall be swept around the resonant frequency as the centre, and the attenuation-frequency characteristics shall be recorded to obtain the Q-value, which corresponds to the loss.

The target relative uncertainty of this method is less than 10 % at temperatures of 30 K to 80 K.

It is the responsibility of the user of this standard to consult and establish safety and health practices and to determine the applicability of regulatory limitations prior to use.

Hazards exist in this type of measurement. The use of a cryogenic system is essential to cool the superconductors to allow transition into the superconducting state. Direct contact of skin with cold apparatus components can cause immediate freezing, as can direct contact with a spilled cryogen. The use of an r.f.-generator is also essential to measure high-frequency

properties of materials. If its power is too high, direct exposure to human bodies can cause an immediate burn.

## 5 Apparatus

### 5.1 Measurement equipment

Figure 1 shows a schematic diagram of the equipment required for the microwave measurement. The equipment consists of a network analyzer system for transmission measurements, a measurement apparatus, and thermometers for monitoring the temperature of HTS films under test.

An incident power generated from a suitable microwave source such as a synthesized sweeper is applied to the dielectric resonator fixed in the measurement apparatus. The transmission characteristics are shown on the display of the network analyzer.

The measurement apparatus is fixed in a temperature-controlled cryocooler.

For measuring the  $Z_S$  of HTS films, a vector network analyzer is recommended because it has better measurement accuracy than a scalar network analyzer due to its wider dynamic range.

### 5.2 Measurement apparatus

Figure 2 shows a schematic diagram of a typical measurement apparatus for the  $Z_S$  of HTS films deposited on a substrate with a flat surface. The lower HTS film is pressed down by a spring, which is made of beryllium copper. Use of a plate type spring is recommended for the improvement of measurement uncertainty. This type of spring reduces the friction between the spring and the other part of the apparatus, and enables smooth motion of HTS films in the course of thermal expansion/contraction of the dielectric-loaded cavity. The upper HTS film is glued to the Cu plate at the top using adhesives with good thermal conductivity.

The  $R_S$  is measured with the upper HTS film being in contact with the top of the Cu cavity. During measurements of the  $R_S$ , the whole resonator is first cooled down to the lowest temperature with the cryocooler turned on and then warmed up to higher temperatures with the cryocooler turned off. Meanwhile, the  $X_S$  is measured with a small gap between the upper HTS film and the top of the Cu cavity. The gap distance shall be set to a value predetermined at the room temperature by using either a micrometer or a step motor connected to the upper superconductor film through a polytetrafluoroethylene (PTFE) rod. The real gap distances would be a little longer at cryogenic temperatures than the corresponding predetermined ones due to thermal contraction of the PTFE rod. The gap distance should be small enough not to cause significant radiation loss and large enough to enable control of the temperature of the upper superconductor film. More detailed descriptions on a dielectric resonator with a movable top plate, a switch block for thermal connection, and the dielectric resonator assembled with the switch block are given in Figures 3 to 5, respectively. Procedures for controlling the temperature of the upper HTS film for measurements of the  $X_S$  are described in 6.6.

Each of the two semi-rigid cables shall have a small loop at the end as shown in Figure 3. The plane of the loop shall be set parallel to that of the HTS films in order to suppress the unwanted  $TM_{mn0}$  modes. The coupling loops shall be carefully checked prior to the measurements to keep the good coupling conditions. These cables can move to the right or to the left to adjust the insertion attenuation ( $IA$ ). In this adjustment, coupling of unwanted cavity modes to the interested dielectric resonance mode shall be suppressed. Unwanted, parasitic coupling to the other modes not only reduces the high-Q value of the TE mode resonator but also increases uncertainty in the measured resonant frequency of the TE mode resonator, making it difficult to measure changes in the resonant frequency vs. temperature data with accuracy.